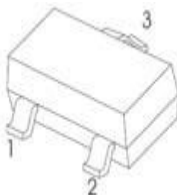
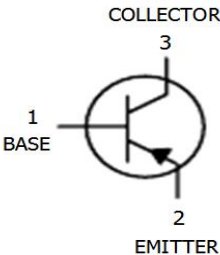


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors																																								
<u>SOT-23</u>   1.BASE 2.EMITTER 3.COLLECTOR	Features • Ideally suited for automatic insertion • Epitaxial planar die construction • Complementary NPN type available(BC817)																																								
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted) <table><tr><th>Parameter</th><th>Symbol</th><th>Value</th><th>Unit</th></tr><tr><td>Collector-Base Voltage</td><td>VCBO</td><td>-50</td><td>V</td></tr><tr><td>Collector-Emitter Voltage</td><td>VCEO</td><td>-45</td><td>V</td></tr><tr><td>Emitter-Base Voltage</td><td>VEBO</td><td>-5</td><td>V</td></tr><tr><td>Collector Current -Continuous</td><td>IC</td><td>-500</td><td>mA</td></tr><tr><td>Collector Current -Pulsed</td><td>ICM</td><td>-200</td><td>mA</td></tr><tr><td>Collector Power Dissipation</td><td>PC</td><td>300</td><td>mW</td></tr><tr><td>Thermal Resistance From Junction To Ambient</td><td>RθJA</td><td>417</td><td>℃/W</td></tr><tr><td>Junction Temperature</td><td>Tj</td><td>150</td><td>℃</td></tr><tr><td>Storage Temperature</td><td>Tstg</td><td>-55~+150</td><td>℃</td></tr></table>		Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	-50	V	Collector-Emitter Voltage	VCEO	-45	V	Emitter-Base Voltage	VEBO	-5	V	Collector Current -Continuous	IC	-500	mA	Collector Current -Pulsed	ICM	-200	mA	Collector Power Dissipation	PC	300	mW	Thermal Resistance From Junction To Ambient	RθJA	417	℃/W	Junction Temperature	Tj	150	℃	Storage Temperature	Tstg	-55~+150	℃
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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -10μA, IE=0	-50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -10mA, IB=0	-45			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-10μA, IC=0	-6			V
Collector cut-off current	ICBO	VCB= -45 V , IE=0			-0.1	μA
Collector cut-off current	ICEO	VCE= -40V , IB=0			-0.8	μA
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.1	μA
DC current gain	hFE	VCE= -1V, IC= -100mA	100		600	
	hFE	VCE= -1V, IC= -500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC= -500mA, IB= -5mA			-0.65	V
Base-emitter saturation voltage	VBE(sat)	IC= -500 mA, IB= -5mA			-1.2	V
Transition frequency	fT	VCE= -5V, IC= -10mA f=100MHz	100			MHz
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		10		PF

CLASSIFICATION OF hFE

Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-600
Marking	5A	5B	5C

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

